Preliminary

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT6L62AS

VHF-UHF Band Low Noise Amplifier Application VHF-UHF Band Oscillator Application

 Two devices are built into the sES6 package, which is smaller and thinner than the super-thin and ultra-super mini (6-pin) ES6 package.

Mounted Devices

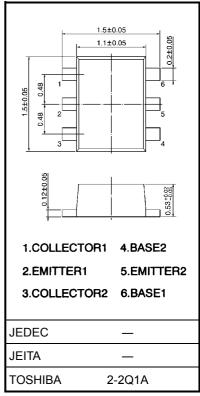
	Q1	Q2
Three pin SSM type part No.	MT3S07S	MT3S03AS

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rat	Unit	
Characteristics		Q1	Q2	Offic
Collector-base voltage	V _{CBO}	10	10	V
Collector-emitter voltage	V _{CEO}	5	5	V
Emitter-base voltage	V _{EBO}	1.5	2	V
Collector current	IC	25	40	mA
Base current	ΙΒ	10	10	mA
Collector power dissipation	P _C (Note 1)	150		mW
Junction temperature	Tj	125		°C
Storage temperature range	T _{stg}	-55~125		°C

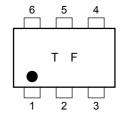
Note 1: Total power dissipation of Q1 and Q2 mounted on the circuit board.

Unit: mm

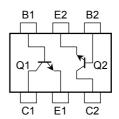


Weight: 2.1 mg

Marking



Pin Assignment



Electrical Characteristics Q1-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 5 \text{ V}, I_{E} = 0$	_	_	0.1	μА
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 \text{ V, } I_C = 0$	_	_	1	μА
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$	70	_	140	_
Transition frequency	f _T	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$	10	12	_	GHz
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	6.5	_	- dB
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, I_{C} = 15 \text{ mA}, f = 2 \text{ GHz}$	4	7	_	
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.6	3	- dB
	NF (2)	$V_{CE} = 3 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.5	3	
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note 2)	_	0.45	0.85	pF

Electrical Characteristics Q2-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 5 \text{ V}, I_{E} = 0$	_	_	0.1	μА
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 \text{ V, } I_{C} = 0$	_	_	1	μА
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$	80	_	160	_
Transition frequency	f _T (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$	5	7	_	GHz
	f _T (2)	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$	7	10	_	
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	5	_	dB
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, I_{C} = 20 \text{ mA}, f = 2 \text{ GHz}$	3	6.5	_	
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.7	3	dB
	NF (2)	$V_{CE} = 3 \text{ V}, I_{C} = 7 \text{ mA}, f = 2 \text{ GHz}$	_	1.4	2.2	uБ
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note 2	<u> </u>	0.8	1.15	pF

Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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